

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor device includes the steps of forming a stress relief layer on a wafer such that the stress relief layer is away from at least part of electrodes formed on the wafer; forming a wiring layer in which lines that extend from the electrodes to the stress relief layer are formed; forming outer electrodes that are over the stress relief layer and are connected to the lines in the wiring layer; and forming a dielectric layer by applying dielectric liquid by an inkjet method to portions in the lines where the outer electrodes are connected to form a capacitor. The step of forming the dielectric layer is conducted after the step of forming the wiring layer.